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(54) **TRANSPARENT OHMIC CONTACTS ON  
LIGHT EMITTING DIODES WITH CARRIER  
SUBSTRATES**

(75) Inventors: **John A. Edmond**, Cary, NC (US);  
**David B. Slater, Jr.**, Durham, NC  
(US); **Michael J. Bergmann**, Chapel  
Hill, NC (US)

(73) Assignee: **CREE, INC.**, Durham, NC (US)

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See application file for complete search history.

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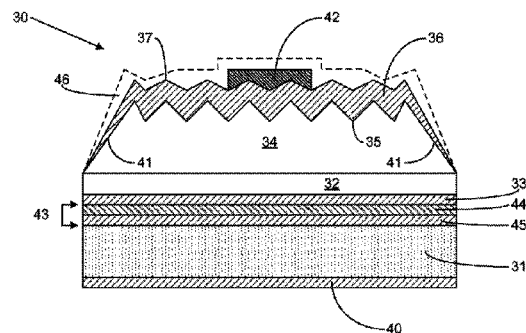
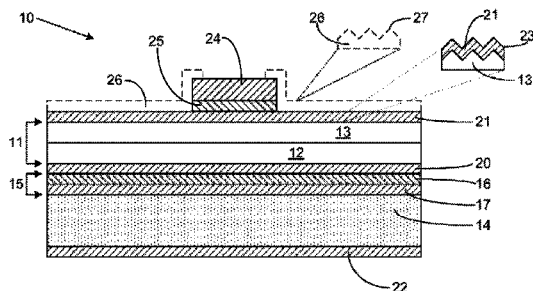
(74) *Attorney, Agent, or Firm* — Koppel, Patrick, Heybl  
& Philpott

(57)

**ABSTRACT**

A light emitting diode is disclosed that includes an active structure formed of at least p-type and n-type epitaxial layers of Group III nitride on a conductive carrier substrate. A conductive bonding system joins the active structure to the conductive carrier substrate. A first transparent ohmic contact is on the active structure adjacent the conductive carrier substrate, a second transparent ohmic contact is on the active structure opposite the conductive carrier substrate, and a third ohmic contact is on the conductive carrier substrate opposite from the active structure.

**46 Claims, 2 Drawing Sheets**



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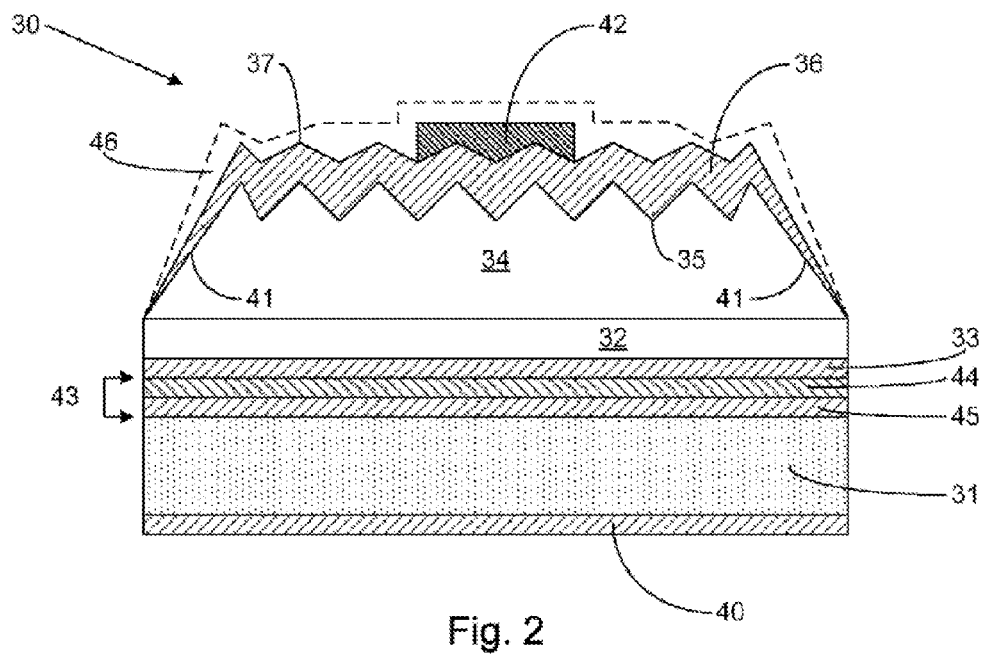
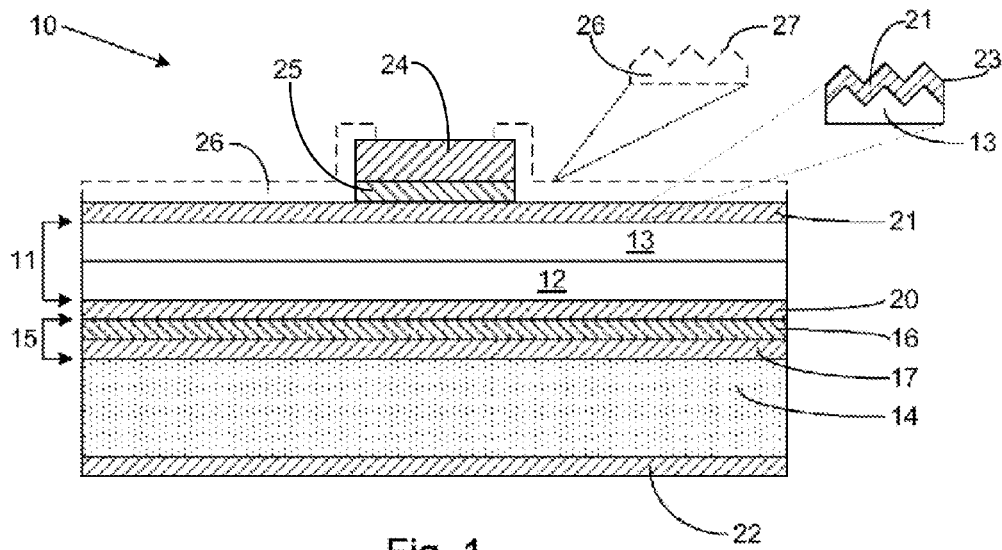
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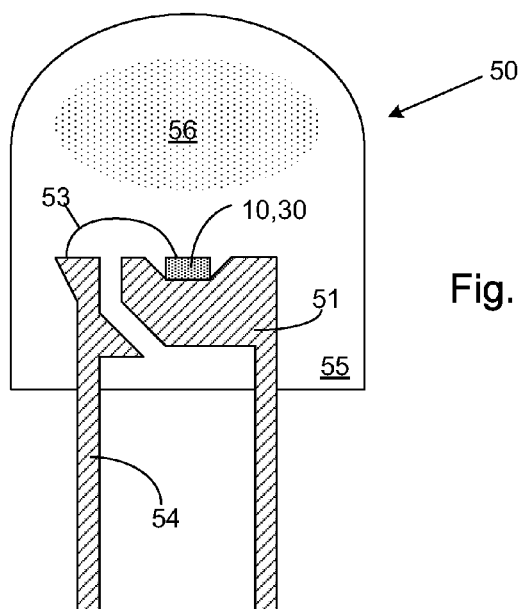


Fig. 3

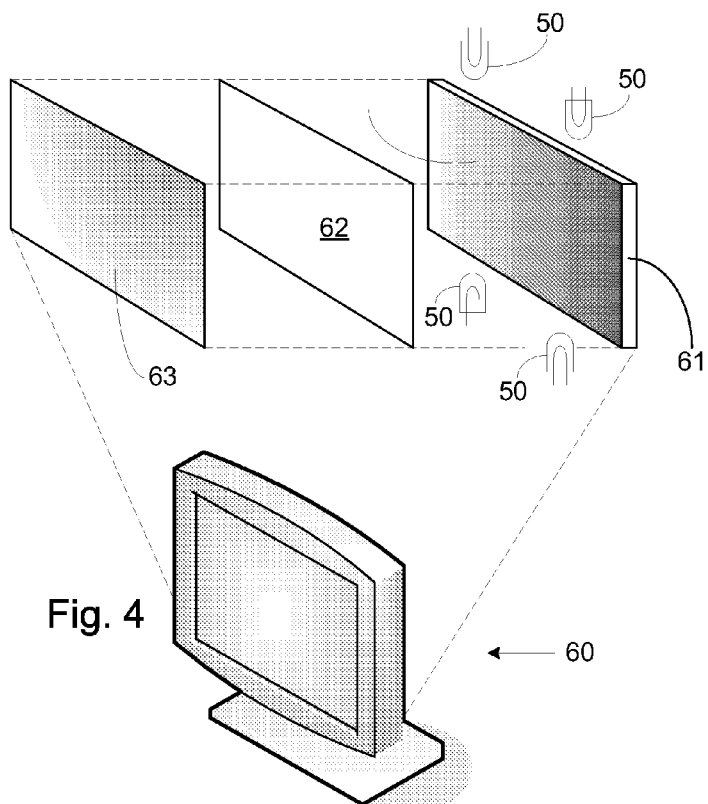


Fig. 4

# TRANSPARENT OHMIC CONTACTS ON LIGHT EMITTING DIODES WITH CARRIER SUBSTRATES

## RELATED APPLICATIONS

This is related to copending and commonly assigned application Ser. No. 11/738,122 filed concurrently herewith for "Transparent Ohmic Contacts on Light Emitting Diodes with Growth Substrates."

## BACKGROUND

The present invention relates to light emitting diodes and in particular relates to increasing the external quantum efficiency of light emitting diodes in which a growth substrate has been partially or entirely removed, and a carrier substrate has been added.

Light emitting diodes (LEDs) are a class of photonic semiconductor devices that convert an applied voltage into light by encouraging electron-hole recombination events in an appropriate semiconductor material. In turn, some or all of the energy released in the recombination event produces a photon.

Light emitting diodes share a number of the favorable characteristics of other semiconductor devices. These include generally robust physical characteristics, long lifetime, high reliability, and, depending upon the particular materials, low cost.

A number of terms are used herein that are common and well-understood in the industry. In such industry use, however, these terms are sometimes informally blended in their meaning. Accordingly, these terms will be used as precisely as possible herein, but in every case their meaning will be clear in context.

Accordingly, the term "diode" or "chip" typically refers to the structure that minimally includes two semiconductor portions of opposite conductivity types (p and n) along with some form of ohmic contacts to permit current to flow across the resulting p-n junction when a potential difference is applied.

The term "lamp" is used to designate a light emitting diode that is matched with an appropriate mechanical support and electrical contact and potentially a lens to form a discrete device that can be added to or included in electrical circuits or lighting fixtures or both.

As used herein, the term "package" typically refers to the placement of the semiconductor chip on an appropriate physical and electrical structure (sometimes as simple as a small piece of metal through which the electrical current is applied) along with a plastic lens (resin, epoxy, encapsulant) that provides some physical protection to the diode and can optically direct the light output.

Appropriate references about the structure and operation of light emitting diodes and diode lamps include Sze, *PHYSICS OF SEMICONDUCTOR DEVICES*, 2d Edition (1981) and Schubert, *LIGHT-EMITTING DIODES*, Cambridge University Press (2003).

The color emitted by an LED is largely defined by the material from which it is formed. Diodes formed of gallium arsenide (GaAs) and gallium phosphide (GaP) tend to emit photons in the lower energy (yellow, red, infrared) portions of the spectrum. Materials such as silicon carbide (SiC) and the Group III nitrides have larger bandgaps and thus can generate photons with greater energy that appear in the green, blue, violet and ultraviolet portions of the electromagnetic spectrum.

In some applications, an LED is more useful when its output is moderated or converted to a different color. As the availability of blue-emitting LEDs has greatly increased, the incorporation of yellow-emitting phosphors that down-convert the blue photons has likewise increased. The combination of the blue light emitted by the diode and the yellow light emitted by the phosphor can create white light. In turn, the availability of white light from solid-state sources provides the capability to incorporate them in a number of applications, particularly including illumination and as lighting (frequently backlighting) for color displays. In such devices (e.g., flat computer screens, personal digital assistants, and cell phones), the blue LED and yellow phosphor produce white light which is then distributed in some fashion to illuminate the color pixels. Such color pixels are often formed by a combination of liquid crystals, color filters and polarizers, and the entire unit including the backlighting is generally referred to as a liquid crystal display ("LCD").

As the use of light emitting diodes has commercially increased and as the understanding of the basic characteristics of diodes used to produce white light has matured, the advances of interest in the technology tend to be those that increase the total amount of light that is produced by a given diode structure, all other factors being equal.

In this regard, the number of individual photons produced by a diode in any given amount of time depends upon the number of recombination events occurring in the diode, with the number of photons generally being less than the number of recombination events (i.e., not every event produces a photon). In turn, the number of recombination events depends upon the amount of current applied across the diode. Once again the number of recombination events will typically be less than the number of electrons injected across the junction. Thus, these electronic properties can reduce the external output of the diode.

Additionally, when photons are produced, they must also actually leave the diode and the lamp to be perceived by an observer. Although many photons will leave the lamp without difficulty, a number of well-understood effects prevent some fraction of the photons from leaving. These effects arise from the difference in refractive index of the various materials within the diode, and thus reduce the external output of an LED lamp (i.e., its efficiency). These include internal reflection of a photon until it attenuated and emitted or absorbed (i.e., Snell's Law and Fresnel Loss) rather than emitted. The difference in the index of refraction between the materials in the diode can also change the direction of an emitted photon (Snell's Law) towards an object that subsequently attenuates or absorbs it. The same results can occur for yellow photons that are emitted by the phosphor in a phosphor-containing LED lamp. In an LED lamp such "objects" can include the substrate, parts of the packaging, and the metal contact layers. Indeed, the same quantum mechanical characteristics that permit semiconductor materials to emit photons will also cause them to absorb photons. Thus, even the light emitting epitaxial layers in an LED can absorb emitted photons and reduce the overall external efficiency of the diode.

Many semiconductor devices, including many light emitting diodes, consist in basic form of a semiconductor substrate and epitaxial layers of semiconductor materials on the substrate. The epitaxial layers often (although not necessarily exclusively) form the active portions of the device. They are generally favored for this purpose because they are grown in a manner (frequently chemical vapor deposition) that increases both their chemical purity and produces a highly ordered crystal structure. Additionally, chemical

vapor deposition provides an excellent technique for precisely doping an epitaxial layer. In turn, the appropriate purity, crystal structure and doping are typically desired or necessary for successful operation of the semiconductor device.

The chemical vapor deposition (CVD) and related techniques used to fabricate epitaxial layers are, however, generally more time-consuming than other crystal growth techniques such as sublimation or growth from a melt (sometimes referred to as bulk growth). As a result, these more rapid (comparatively) methods are often used to produce an appropriate crystal when the intended structure is other than an epitaxial layer.

Thus, by combining a bulk-growth substrate with epitaxial layers, an overall structure can be produced with a reasonable combination of crystal structure, compositional purity, doping, and efficient fabrication.

Nevertheless, for several crystal growth-related reasons, bulk (i.e., reasonably large size) single crystals of Group III nitrides are, for practical purposes, unavailable. Accordingly, Group III nitride LEDs are typically formed on other bulk substrate materials, most commonly sapphire ( $\text{Al}_2\text{O}_3$ ) and silicon carbide (SiC). Sapphire is relatively inexpensive, widely available, and highly transparent. Alternatively, sapphire is a poor thermal conductor and therefore less suitable for certain high-power applications. Additionally, in some devices, electrically conductive substrates are preferred and sapphire is insulating rather than conductive. Sapphire also carries a lattice mismatch with (for example) gallium nitride of about 16%.

Silicon carbide has a better thermal conductivity than sapphire and a better lattice match with Group III nitrides; i.e., a mismatch of about 3.5% with gallium nitride and only about 1% with aluminum nitride. Silicon carbide can be conductively doped, but is also much more expensive than sapphire.

Although silicon carbide offers advantages for the growth of Group III nitride epitaxial layers, there are other reasons that encourage the use of other substrate materials in the final diodes. In order to use such other materials, the growth substrate (typically silicon carbide) must be partially or entirely removed and a carrier substrate must be added.

Depending upon the function and use of the final diode, the use of such carrier substrates offers several advantages. As one, the thickness required for a growth substrate during the diode fabrication steps may not be required in the final diode. By removing the growth substrate and replacing it with the carrier substrate, the overall thickness of the diode can be advantageously reduced. This is described in, for example, co-pending and commonly assigned application Ser. No. 10/951,042 filed Sep. 22, 2004 for "High Efficiency Group III Nitride-Silicon Carbide Light Emitting Diode."

As another advantage, replacing the growth substrate with the carrier substrate often results in positioning the carrier substrate on the opposite side of the active layers from the growth substrate. For example, silicon carbide growth substrates are frequently n-type. Thus, the first epitaxial layer grown on the silicon carbide substrate is frequently an n-type Group III nitride layer. The p-type layer is then grown on top of the n-type layer.

The carrier substrate is then typically added to the p-type layer to form an intermediate structure having both substrates (growth and carrier). When the growth substrate is removed from the n-type layer, the carrier substrate remains attached to the p-type layer. The resulting structure has a carrier substrate, a p-type layer on the carrier substrate, and an n-type layer as the portion opposite the carrier substrate.

Although p-type layers are necessary for producing p-n junctions and junction characteristics, the conductivity of p-type Group III nitride materials is comparatively lower than that of n-type layers. As a result, it can be difficult to obtain a desired amount of current spreading in a p-type layer.

By using a carrier substrate, the epitaxial layers can be flipped and the p-type layer can be conductively mounted to the carrier substrate and the n-type layer can form the emitting face of the diode. In this orientation the higher conductivity of the n-type layer offers advantages in lateral current flow and thus light extraction.

As yet another advantage, and although the observation to date has been empirical, increased brightness has been observed from Group III nitride light emitting diodes in which the epitaxial layers are grown on silicon carbide and after which the silicon carbide substrate is removed and replaced with a carrier substrate.

Copending and commonly assigned application Ser. No. 11/338,918 filed Jan. 25, 2006 and now published as No. 20060131599 offers some additional explanations and considerations as to how the substrate can affect the overall device performance.

A carrier substrate can also provide a structure that is more amenable than a silicon carbide substrate to certain soldering techniques or other later fabrication steps.

In other cases, the working diode in context does not require the thermal or electronic or optical properties of silicon carbide. In such cases silicon carbide offers advantages for growth, but not for use. This differs, of course, from certain power devices in which the intrinsic semiconductor characteristics of silicon carbide are the relevant property. Growing Group III nitride epitaxial layers on silicon carbide and then removing the silicon carbide substrate can reduce the overall cost of the resulting diodes, because the removed silicon carbide substrate (which typically is used as a wafer and then is removed as a wafer) can be reused. Thus, although silicon carbide is comparatively more expensive than sapphire or other substrate materials, reusing it in this fashion moderates the cost of fabrication while providing the growth advantages of SiC for Group III nitride epilayers.

For at least these reasons, producing Group III nitride light emitting diodes on carrier substrates after growth substrates have been removed remains of significant interest and drives a desire for continuing improvements in the technology. Additionally, increasing the external quantum efficiency of light emitting diodes within the context of such carrier substrate structures remains a continuing goal.

## SUMMARY

In one aspect, the invention is light emitting diode that includes an active structure formed of at least p-type and n-type epitaxial layers of Group III nitride, a conductive carrier substrate, a conductive bonding system joining the active structure to the conductive carrier substrate, a first transparent ohmic contact to the active structure adjacent the conductive carrier substrate, a second transparent ohmic contact to the active structure opposite the conductive carrier substrate, and a third ohmic contact to the conductive carrier substrate opposite from the active structure.

In another aspect, the invention is a light emitting diode that includes a conductive carrier substrate, a p-type Group III nitride epitaxial layer on the conductive carrier substrate, a first transparent ohmic contact to the p-type layer and between the p-type layer and the conductive carrier substrate, an n-type gallium nitride epitaxial layer on the p-type

gallium nitride layer, a lenticular surface on the n-type gallium nitride epitaxial layer, a second transparent ohmic contact substantially covering the n-type epitaxial layer and the lenticular surface, with the second transparent ohmic contact forming a lenticular surface opposite the n-type epitaxial layer, and a third ohmic contact to the carrier substrate opposite from the Group III nitride layers.

In yet another aspect the invention is a light emitting diode lamp that includes a header, a light emitting diode on the header, with the diode including at least an active structure of n-type and p-type layers of Group III nitride, respective transparent ohmic contact layers on opposite sides of the active structure, a conductive carrier substrate, and an ohmic contact between the conductive carrier substrate and the header, and an encapsulant covering the light emitting diode on the header and portions of the header.

In yet another aspect the invention is a display that includes a light emitting diode lamp, a light diffuser adjacent the lamp, a plurality of liquid crystals adjacent the diffuser, and color filters.

The foregoing and other objects and advantages of the invention and the manner in which the same are accomplished will become clearer based on the followed detailed description taken in conjunction with the accompanying drawings.

## BRIEF DESCRIPTION OF THE DRAWINGS

FIGS. 1 and 2 are cross-sectional schematic diagrams of light emitting diodes according to the present invention.

FIG. 3 is a cross-sectional schematic view of a light emitting diode lamp according to the present invention.

FIG. 4 is a partially exploded schematic view of a display that incorporates diodes and diode lamps according to the present invention.

## DETAILED DESCRIPTION

FIG. 1 illustrates a first embodiment of the diode according to the present invention broadly designated at 10. The diode 10 includes an active structure designated by the brackets 11 that is formed of at least one p-type Group III nitride epitaxial layer 12 and one n-type Group III nitride epitaxial layer. The nature and fabrication of Group III nitride epitaxial layers is generally well understood in this art and will not be otherwise described in detail. Generally (although not exclusively), light emitting layers are formed of gallium nitride (GaN) or indium gallium nitride ( $\text{In}_x\text{Ga}_{1-x}\text{N}$ ), with layers of aluminum gallium nitride ( $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ) used in certain circumstances such as buffer layers. Although FIG. 1 illustrates the light emitting active structure 11 as a straightforward p-n junction between one p-type layer 12 and one n-type layer 13, it will be understood that the active structure 11 could include additional layers such as a quantum well, multiple quantum wells, or single or double heterostructures. Again, these are well understood in the art and will not be described in detail.

The diode 10 includes a conductive carrier substrate 14. The carrier substrate 14 can be any material that can be conductively doped (or is conductive, such as a metal), that is compatible with normal fabrication steps and that will otherwise support and complement the operation of the light emitting active structure 11. Appropriate conductive carrier structures include silicon and silicon carbide, as well as any other material that otherwise meets the noted qualifications.

Because the carrier substrate 14 is not the original growth substrate, a conductive bonding system indicated by the

brackets 15 joins the active structure 11 to the conductive carrier substrate 14. FIG. 1 illustrates the bonding system as two metal layers 16 and 17 respectively, but it will be understood that in some cases a single layer may be appropriate while another circumstances, a larger number of layers can provide advantages. Examples of the nature and fabrication of appropriate metal bonding layers are set forth in co-pending and commonly assigned application Ser. No. 11/428,158 filed Jun. 30, 2006 for "Nickel-Tin Bonding System for Semiconductor Wafers and Devices;" and Ser. No. 11/534,317 filed Sep. 22, 2006 for "Modified Gold-Tin System with Increased Melting Temperature for Wafer Bonding." The contents of these are incorporated entirely here by reference and it will be understood that these are illustrative, rather than limiting, of the claimed invention.

The diode 10 includes a first transparent ohmic contact 20 to the active structure 11 adjacent the conductive carrier substrate 14. A second transparent ohmic contact 21 is on the active structure 11 opposite from the conductive carrier substrate 14. A third ohmic contact 22 is made to the opposite side of the conductive carrier substrate 14 and completes the basic structure.

As used herein, the term "transparent" refers to an ohmic contact that will transmit at least about 70 percent of incident light of the frequencies generated by the diode 10 and preferably 90-100 percent of such light.

The most common material for a transparent ohmic contact to group three nitride layers (and other semiconductor materials) is indium tin oxide (ITO), and each of the respective ohmic contacts can be formed of indium tin oxide. Other candidate materials include the following: indium tin oxide, nickel oxide, zinc oxide, cadmium tin oxide, titanium tungsten nickel, indium oxide, tin oxide, magnesium oxide,  $\text{ZnGa}_2\text{O}_4$ ,  $\text{SnO}_2/\text{Sb}$ ,  $\text{Ga}_2\text{O}_3/\text{Sn}$ ,  $\text{AgInO}_2/\text{Sn}$ ,  $\text{In}_2\text{O}_3/\text{Zn}$ ,  $\text{CuAlO}_2$ ,  $\text{LaCuOS}$ ,  $\text{CuGaO}_2$ , and  $\text{SrCu}_2\text{O}_2$ . Although the third ohmic contact 22 is not necessarily transparent, it can be made transparent and when transparent can be made from this same group of materials.

FIG. 1 also illustrates that the first and second ohmic contacts 20 and 21 cover substantially all of the relevant portions of the active layer 11. This helps with current spreading, particularly with respect to the p-type layer 12.

The transparent ohmic contacts 20 and 21 (and potentially the ohmic contact 22 to the substrate 14) can also be formed of a plurality of layers of different transparent materials that have different refractive indices. By providing a progressive refractive index through the contact, such a structure minimizes Fresnel loss as light travels through the contact.

A similar advantage can be obtained by an indium tin oxide contact in which the amount of indium is graded through the contact to progressively change the refractive index and minimize Fresnel loss as light travels through the contact.

The diode 10 can also include at least one reflective layer between or adjacent the substrate 14 and the active portion 11. Such a reflective layer can include one of the bonding metals 16 or 17, the substrate itself 14, or additional layers (not shown) adjacent the bonding layers, or even combinations of these reflective layers.

The light emitting diode 10 can also include a lenticular surface illustrated at 23 in the enlarged breakout portion illustration showing a portion of the n-type layer 13 and the second ohmic contact 21.

Exemplary (but not limiting) techniques and resulting lenticular surfaces are set forth in copending and commonly assigned application Ser. No. 11/082,470 filed Mar. 17, 2005 for "High Efficiency Group III Nitride LED with Lenticular



Surface;" Ser. No. 11/461,018 filed Jul. 31, 2006 for "Method of Forming 3D Features on LEDs For Improved Light Extraction;" and Ser. No. 11/343,180 filed Jan. 30, 2006 for, "Improved External Extraction Light Emitting Diode Based Upon Crystallographic Faceted Surfaces." The contents of each of these applications are incorporated entirely herein by reference. As respectively indicated therein, such lenticular surfaces can be generated with an embossing technique or chemically developed. Such lenticular surfaces are sometimes referred to as being "roughened" or "textured" surfaces.

In typical embodiments, the diode **10** includes a bond pad **24** to the second transparent ohmic contact **21**. In turn, the bond pad **24** can also include a reflective layer **25** that reflects light away from the bond pad.

Although reflecting the light back into the active layers has some disadvantages (because these layers absorb photons for reasons directly related to their emission of photons), the bond pad **24** is typically the part of the diode that is most highly absorbing of emitted photons. Thus, reflecting photons from the bond pad **24** almost always increases light extraction.

FIG. **1** further illustrates that the diode **10** can optionally include a passivation layer indicated by the dotted section at **26**. Silicon nitride is an exemplary passivation structure as are combinations of silicon nitride and silicon dioxide ( $\text{SiO}_2$ ) or silicon oxynitride. The silicon nitride can be stoichiometric ( $\text{Si}_3\text{N}_4$ ) or non-stoichiometric, and is preferably sputter-deposited in order to minimize or eliminate hydrogen from being incorporated in the layer. Generally speaking, the presence of hydrogen adversely affects the characteristics of some Group III nitride layers. As illustrated by the enlarged section, the passivation layer **26** can optionally include a lenticular surface **27**.

As FIG. **1** illustrates, environmental protection represents at least one of the reasons for including the passivation layer **26**. Thus, the passivation layer **26** covers substantially all of the second ohmic contact **21**.

FIG. **2** shows a second embodiment of a light emitting diode according to the invention broadly designated at **30**. The diode **30** includes a conductive carrier substrate **31** with a p-type epitaxial Group III nitride layer **32** on the conductive carrier substrate **31**.

As used herein, the term "on" refers to the relative positions of elements in the diode. Although the meaning will be clear in context, particularly when taken in conjunction with the drawings, the description of a layer being "on" another layer can include situations in which the layers touch, or in which they are above and below one another. Where required for clarity, layers that touch will be described as such, but generally the structure will be clear in context.

A first transparent ohmic contact **33** provides electrical contact between the p-type layer **32** and the conductive carrier substrate **31**. An n-type gallium nitride epitaxial layer **34** is on the p-type gallium nitride layer **32**. The n-type layer **34** has a lenticular surface **35**.

A second transparent ohmic contact **36** substantially covers the entire n-type epitaxial layer **34** and the lenticular surface **35**. The second transparent ohmic contact **36** also forms a lenticular surface **37** opposite the n-type epitaxial layer **34**. The lenticular surface **37** (all in the epitaxial layer **34**) can be the same as (i.e., conforming to) the lenticular surface of the epitaxial layer, or it can be different from the lenticular surface **35**.

The same relationships can apply when the emitting portion of the diode is p-type; i.e., the p-type layer of Group

III nitride can include the lenticular surface with the transparent metal ohmic contact on the lenticular p-type layer also having a lenticular surface. In the same manner, the lenticular surface of the ohmic contact can either be the same as (i.e., conforming to) the lenticular surface of the epitaxial layer, or it can have a different lenticular pattern.

The transparent ohmic contacts **33** and **36** can have any of the characteristics referred to with respect to FIG. **1**, and are selected from the same groups of materials. As in the first embodiment, the contacts can potentially include a plurality of layers that progress in their respective refractive indices or an ITO layer graded with respect to the atomic fraction of indium.

A third ohmic contact **40** is on the conductive carrier substrate opposite from the Group III nitride layers **34** and **32**.

The embodiment illustrated in FIG. **2** includes beveled sidewalls **41** that help increase the external extraction of light from the epitaxial layers. Such shaping is set forth in detail in parent application Ser. No. 11/338,918. Although the shaping of the substrate can include a variety of geometry choices, a straightforwardly beveled sidewall as indicated in FIG. **2** is appropriate in many circumstances.

As in the first embodiment, the diode **30** can include a bond pad **42** in electrical contact with the second transparent ohmic contact **36**. Although not illustrated in FIG. **2**, the bond pad **42** can also include a reflective layer or reflective surface to minimize or eliminate the absorption of light by the bond pad **42**.

A bonding system shown by the brackets **43** joins the epitaxial layers **34** and **32** with the conductive carrier substrate **31**. Two metal bonding layers **44** and **45** are illustrated. As in the case of the first embodiment, however, it will be understood that in some cases the ohmic layer **33** could serve to join the substrate **31** to the epitaxial layers **32** and **34**, or that in other cases the bonding system could be other than a metal provided it was sufficiently conductive. Similarly, the bonding structure **43** can be limited to a single layer, or it can include a plurality of layers.

As in the first embodiment, the diode **30** can include a reflective layer or reflective surface typically selected from the group consisting of one of the bonding metal layers **44** or **45** or the conductive carrier substrate **31**.

In a manner similar to the conductive carrier substrate **14** shown in FIG. **1**, the conductive carrier substrate **31** can comprise a material that is suitable for the structure and function of the diode, but is most typically selected from the group consisting of silicon, silicon carbide, gallium arsenide and metals.

As in the earlier embodiment, the diode **30** illustrated in FIG. **2** includes a passivation layer **46** that covers the second transparent ohmic contact **36** and the bond pad **42**. Exemplary compositions for the passivation layer **46** includes silicon nitride (both stoichiometric and nonstoichiometric, potentially silicon dioxide, and in some cases advantageous combinations of layers of silicon nitride and silicon dioxide).

FIG. **3** is a schematic diagram of a light emitting diode lamp **50** according to the present invention. The lamp **50** includes a light emitting diode according to the invention which can include either of the embodiments **10** or **20** described with respect to FIGS. **1** and **2**.

The diode **10** is positioned on a header **51** which forms a mechanical support and electrical contact to the diode **10**. The header **51** also acts as an electrode for the lamp **50**. A wire **53** provides electrical contact to a second electrode **54**.

The term “header” is used in a broad sense to describe an appropriate electromechanical support for an LED in the context of a lamp.

An encapsulant **55** covers the LED **10** and portions of the header **51** and the electrode **54**. The encapsulant **55** provides a lens for the lamp **50**, and also provides environmental protection to the diode **10**. The encapsulant can be any material that is suitable for the purposes of the invention and that does not otherwise interfere with the operation of the LED chip or the other elements of the lamp. As set forth in co-pending and commonly assigned application Ser. No. 60/824,385 filed Sep. 1, 2006 for, “Phosphor Position In Light Emitting Diodes,” when the LED chip emits in the higher energy portions of the spectrum (e.g., blue, violet, and ultraviolet), the encapsulant should be less reactive or inert to the photons emitted at such frequencies. Thus, polysiloxane (“silicone”) resins tend to be particularly well suited for the encapsulant. In general, the term polysiloxane refers to any polymer constructed on a backbone of  $-(\text{Si}-\text{O})_n-$  (typically with organic side groups). The term “resin” is used in a broad sense to refer to any polymer, copolymer or composite from which the package can be formed. These materials are generally well understood by those of ordinary skill in the art and need not be discussed in detail.

As set forth earlier, in certain embodiments, the encapsulant contains a phosphor indicated by the shaded portion **56** which typically down-converts the light emitted by the diode **10**. Most typically, because the Group III nitride material system emits in the blue portion of the spectrum, the phosphor **56** responds to the blue frequencies and emits primarily (although not exclusively) in the yellow portion of the visible spectrum. The combination of the blue light from the diode **10** and the yellow light from the phosphor **56** produces an external emission of white light. Cerium-doped yttrium aluminum garnet (YAG) is an exemplary phosphor for this purpose.

FIG. 4 illustrates that several lamps **50** according to the invention can be incorporated into a display broadly designated at **60**. The nature and operation of various displays is generally well-understood and will not be described in detail herein other than to point out that they typically include the diode lamp **50** and a light distributor **61** which both diffuses light in its main plane, and also redirects some of the light perpendicularly to its main plane.

In many circumstances, the display will also include a set of liquid crystals schematically designated by the rectangle **62**, and an appropriate set of one or more color filters schematically illustrated by the single rectangle **63**. Other elements can be included in the display, but are omitted here for the sake of clarity. The liquid crystals generally operate in and “on” or “off” orientation when a signal is applied to them, so that in combination with the color filters **63** the display **60** produces a color image.

In the drawings and specification there has been set forth a preferred embodiment of the invention, and although specific terms have been employed, they are used in a generic and descriptive sense only and not for purposes of limitation, the scope of the invention being defined in the claims.

The invention claimed is:

1. A light emitting diode comprising:

an active structure comprising p-type and n-type epitaxial layers of Group III nitride, wherein the active structure comprises a first lenticular surface;  
an electrically conductive carrier substrate;

an electrically conductive bonding system joining said active structure to said electrically conductive carrier substrate;

a first transparent ohmic contact to said active structure, said first transparent ohmic contact between said active structure and said electrically conductive carrier substrate;

a second transparent ohmic contact in direct contact with said active structure, without any layer in between said active structure and said second transparent ohmic contact, said active structure between said second transparent ohmic contact and said electrically conductive carrier substrate; and

a third ohmic contact to said electrically conductive carrier substrate, said electrically conductive carrier substrate between said third ohmic contact and said active structure,

wherein said second transparent ohmic contact comprises a second lenticular surface opposite the first lenticular surface of the active structure.

2. A light emitting diode according to claim 1 wherein said Group III nitride epitaxial layers are selected from the group consisting of gallium nitride and indium gallium nitride.

3. A light emitting diode according to claim 1 wherein said first transparent ohmic contact and said second transparent ohmic contact comprise indium tin oxide.

4. A light emitting diode according to claim 1 wherein said first transparent ohmic contact and said second transparent ohmic contact are selected from the group consisting of: indium tin oxide, nickel oxide, zinc oxide, cadmium tin oxide, titanium tungsten nickel, indium oxide, tin oxide, magnesium oxide,  $\text{ZnGa}_2\text{O}_4$ ,  $\text{SnO}_2/\text{Sb}$ ,  $\text{Ga}_2\text{O}_3/\text{Sn}$ ,  $\text{AgInO}_2/\text{Sn}$ ,  $\text{In}_2\text{O}_3/\text{Zn}$ ,  $\text{CuAlO}_2$ ,  $\text{LaCuOS}$ ,  $\text{CuGaO}_2$ , and  $\text{SrCu}_2\text{O}_2$ .

5. A light emitting diode according to claim 1 wherein said electrically conductive bonding system comprises at least one metal layer.

6. A light emitting diode according to claim 1 further comprising at least one reflective layer selected from the group consisting of: a bonding layer; said electrically conductive carrier substrate; additional layers adjacent said bonding layer; and combinations thereof.

7. A light emitting diode according to claim 1 wherein said third ohmic contact to said electrically conductive carrier substrate is transparent.

8. A light emitting diode according to claim 7 wherein said third ohmic contact is selected from the group consisting of indium tin oxide, nickel oxide, zinc oxide, cadmium tin oxide, titanium tungsten nickel, indium oxide, tin oxide, magnesium oxide,  $\text{ZnGa}_2\text{O}_4$ ,  $\text{SnO}_2/\text{Sb}$ ,  $\text{Ga}_2\text{O}_3/\text{Sn}$ ,  $\text{AgInO}_2/\text{Sn}$ ,  $\text{In}_2\text{O}_3/\text{Zn}$ ,  $\text{CuAlO}_2$ ,  $\text{LaCuOS}$ ,  $\text{CuGaO}_2$ , and  $\text{SrCu}_2\text{O}_2$ .

9. A light emitting diode according to claim 1 further comprising a bond pad to said second transparent ohmic contact.

10. A light emitting diode according to claim 9 further comprising a reflective layer between said bond pad and said second transparent ohmic contact for reflecting light off said bond pad.

11. A light emitting diode according to claim 1 wherein at least one of said first transparent ohmic contact and said second transparent ohmic contact comprises a plurality of layers that progress in refractive index with respect to one another to minimize Fresnel loss as light travels through said first transparent ohmic contact and said second transparent ohmic contact.

12. A light emitting diode according to claim 1 wherein at least one of said first transparent ohmic contact and said

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second transparent ohmic contact comprises indium tin oxide in which the amount of indium is graded through the contact to progressively change the refractive index and minimize Fresnel loss as a light travels through said first transparent ohmic contact and said second transparent ohmic contact.

13. A light emitting diode according to claim 1 further comprising a passivation layer on said second transparent ohmic contact.

14. A light emitting diode according to claim 13 wherein said passivation layer is selected from the group consisting of silicon nitride, silicon dioxide and silicon oxynitride and covers said second transparent ohmic contact and said active structure.

15. A light emitting diode according to claim 13 wherein said passivation layer comprises stoichiometric silicon nitride.

16. A light emitting diode comprising:

- an electrically conductive carrier substrate;
- a p-type epitaxial layer on said electrically conductive carrier substrate;
- a first transparent ohmic contact between said p-type layer and said electrically conductive carrier substrate;
- an n-type epitaxial layer on said p-type layer;
- a lenticular surface on said n-type epitaxial layer;
- a second transparent ohmic contact covering said n-type epitaxial layer and said lenticular surface;
- said second transparent ohmic contact forming a lenticular surface opposite said n-type epitaxial layer; and
- a third ohmic contact to said electrically conductive carrier substrate opposite from said epitaxial layers wherein said first transparent ohmic contact comprises a second lenticular surface opposite the first lenticular surface of the active structure.

17. A light emitting diode according to claim 16 wherein said third ohmic contact to said electrically conductive carrier substrate is transparent.

18. A light emitting diode according to claim 17 wherein said third ohmic contact is selected from the group consisting of: indium tin oxide, nickel oxide, zinc oxide, cadmium tin oxide, titanium tungsten nickel, indium oxide, tin oxide, magnesium oxide,  $\text{ZnGa}_2\text{O}_4$ ,  $\text{SnO}_2/\text{Sb}$ ,  $\text{Ga}_2\text{O}_3/\text{Sn}$ ,  $\text{AgInO}_2/\text{Sn}$ ,  $\text{In}_2\text{O}_3/\text{Zn}$ ,  $\text{CuAlO}_2$ ,  $\text{LaCuOS}$ ,  $\text{CuGaO}_2$ , and  $\text{SrCu}_2\text{O}_2$ .

19. A light emitting diode according to claim 16 wherein at least one of said first transparent ohmic contact and said second transparent ohmic contact are selected from the group consisting of: indium tin oxide, nickel oxide, zinc oxide, cadmium tin oxide, titanium tungsten nickel, indium oxide, tin oxide, magnesium oxide,  $\text{ZnGa}_2\text{O}_4$ ,  $\text{SnO}_2/\text{Sb}$ ,  $\text{Ga}_2\text{O}_3/\text{Sn}$ ,  $\text{AgInO}_2/\text{Sn}$ ,  $\text{In}_2\text{O}_3/\text{Zn}$ ,  $\text{CuAlO}_2$ ,  $\text{LaCuOS}$ ,  $\text{CuGaO}_2$ , and  $\text{SrCu}_2\text{O}_2$ .

20. A light emitting diode according to claim 16 further comprising a bond pad to said second transparent ohmic contact.

21. A light emitting diode according to claim 16 further comprising bonding layers between said first transparent ohmic contact and said electrically conductive carrier substrate.

22. A light emitting diode according to claim 21 wherein said bonding layers comprise at least one metal layer.

23. A light emitting diode according to claim 22 further comprising a reflective layer selected from the group consisting of one of said bonding metal layers and said electrically conductive carrier substrate.

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24. A light emitting diode according to claim 16 wherein said electrically conductive carrier substrate is selected from the group consisting of silicon, silicon carbide, gallium arsenide and metals.

25. A light emitting diode according to claim 16 further comprising a passivation layer covering said second transparent ohmic contact.

26. A light emitting diode according to claim 25 wherein said passivation layer comprises silicon nitride.

27. A light emitting diode according to claim 16 wherein at least one of said first transparent ohmic contact and said second transparent ohmic contact comprises a plurality of layers of transparent material with progressing indexes of refraction for minimizing Fresnel loss as light passes through said first transparent ohmic contact and said second transparent ohmic contact.

28. A light emitting diode according to claim 16 wherein at least one of said first transparent ohmic contact and said second transparent ohmic contact comprises a layer of indium tin oxide in which the content of indium is progressively graded across the contact to minimize Fresnel loss as light passes through said first transparent ohmic contact and said second transparent ohmic contact.

29. A light emitting diode comprising:

- an active structure comprising p-type and n-type epitaxial layers of Group III nitride, the active structure comprising a lenticular surface;
- an electrically conductive carrier substrate;
- an electrically conductive bonding system joining said active structure to said electrically conductive carrier substrate;
- a first transparent ohmic contact to said active structure;
- a second transparent ohmic contact in direct contact with said lenticular surface of said active structure, without any layer in between said active structure and said second transparent ohmic contact, said active structure between said second transparent ohmic contact and said electrically conductive carrier substrate, wherein said second transparent ohmic contact comprises a progressive refractive index; and
- a third ohmic contact to said electrically conductive carrier substrate, said electrically conductive carrier substrate between said third ohmic contact and said active structure.

30. In a light emitting diode that includes an electrically conductive carrier substrate and a Group III nitride active portion, the improvement comprising:

- an n-type layer of Group III nitride including a lenticular surface;
- a transparent metal ohmic contact in direct contact with said lenticular surface, without any layer in between said lenticular surface and said transparent metal ohmic contact, in which the transparent metal ohmic contact comprises a progressive refractive index; and
- an electrically conductive bonding system between the electrically conductive carrier substrate and the Group III nitride active portion.

31. A light emitting diode according to claim 1, wherein said first transparent ohmic contact is adjacent to said active structure.

32. A light emitting diode according to claim 16, wherein said second transparent ohmic contact is adjacent to said n-type epitaxial layer.

33. A light emitting diode according to claim 29, wherein said first transparent ohmic contact is adjacent to said active structure.

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34. A light emitting diode according to claim 29, wherein said electrically conductive bonding system comprises at least one metal layer.

35. A light emitting diode according to claim 29, wherein said electrically conductive bonding system comprises a first metal layer and second metal layer.

36. A light emitting diode according to claim 29, wherein said second transparent ohmic contact includes a lenticular surface.

37. A light emitting diode according to claim 29, wherein said n-type epitaxial layer includes a lenticular surface.

38. A light emitting diode according to claim 29, further comprising:

a bond pad to said second transparent ohmic contact.

39. A light emitting diode according to claim 38, wherein said bonding pad includes a reflective layer.

40. A light emitting diode according to claim 29, further comprising:

a passivation layer on said second transparent ohmic contact.

41. A light emitting diode according to claim 30, further comprising:

a bond pad to said transparent metal ohmic contact.

42. A light emitting diode according to claim 30, further comprising:

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a passivation layer on said transparent metal ohmic contact.

43. A light emitting diode according to claim 30, further comprising:

a p-type layer of Group III nitride; and

a second metal ohmic contact in direct contact with said p-type layer, without any layer in between said p-type layer and said second metal ohmic contact.

44. A light emitting diode according to claim 30, wherein said electrically conductive bonding system comprises a conductive bonding metal.

45. A light emitting diode according to claim 30, further comprising:

a third metal ohmic contact in direct contact with said electrically conductive carrier substrate, without any layer in between said electrically conductive carrier substrate and said third metal ohmic contact.

46. A light emitting diode according to claim 30, further comprising:

a reflective layer on said transparent metal ohmic contact; and

a bond pad on said reflective layer.

\* \* \* \* \*